# Designer's™ Data Sheet

# Complementary NPN-PNP Silicon Power Bipolar Transistor

The MJ3281A and MJ1302A are PowerBase power transistors for high power audio, disk head positioners and other linear applications.

- Designed for 100 W Audio Frequency
- Gain Complementary:
  - Gain Linearity from 100 mA to 7 A
  - High Gain 60 to 175
  - hFE = 45 (Min) @ IC = 8 A
- Low Harmonic Distortion
- High Safe Operation Area 1 A/100 V @ 1 sec
- High f<sub>T</sub> 30 MHz Typical

# NPN MJ3281A\* PNP MJ1302A\*

\*Motorola Preferred Device

15 AMPERE
COMPLEMENTARY
SILICON POWER
TRANSISTORS
200 VOLTS
250 WATTS



CASE 1-07 TO-204AA (TO-3)

## **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	200	Vdc
Collector–Base Voltage	V <sub>CBO</sub>	200	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	7	Vdc
Collector–Emitter Voltage — 1.5 V	VCEX	200	Vdc
Collector Current — Continuous — Peak (1)	IC	15 25	Adc
Base Current — Continuous	IB	1.5	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	PD	250 1.43	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	°C/W

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle <10%.

**Designer's Data for "Worst Case" Conditions** — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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Preferred devices are Motorola recommended choices for future use and best overall value.



# MJ3281A MJ1302A

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector–Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	VCEO(sus)	200	_	_	Vdc
Emitter–Base Voltage ( $I_E = 100 \mu Adc, I_C = 0$ )	V <sub>EBO</sub>	7	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 200 Vdc, I <sub>E</sub> = 0)	ICBO	_	_	50	μAdc
Emitter Cutoff Current (VEB = 5 Vdc, IC = 0)	IEBO	_	_	5	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 7 Vdc, I <sub>C</sub> = 0)	IEBO	_	_	25	μAdc
SECOND BREAKDOWN			•	•	
Second Breakdown Collector with Base Forward Biased (VCE = 50 Vdc, t = 1 s (non–repetitive) (VCE = 100 Vdc, t = 1 s (non–repetitive)	I <sub>S/b</sub>	4 1	_		Adc
ON CHARACTERISTICS			•	•	•
DC Current Gain (IC = 100 mAdc, VCE = 5 Vdc) (IC = 1 Adc, VCE = 5 Vdc) (IC = 3 Adc, VCE = 5 Vdc) (IC = 5 Adc, VCE = 5 Vdc) (IC = 7 Adc, VCE = 5 Vdc) (IC = 8 Adc, VCE = 5 Vdc) (IC = 15 Adc, VCE = 5 Vdc)	hFE	60 60 60 60 60 45	125 — — — 115 — 35	175 175 175 175 175 175 —	
Collector–Emitter Saturation Voltage (IC = 10 Adc, I <sub>B</sub> = 1 Adc)	VCE(sat)	_	_	3	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 5 Vdc, f <sub>test</sub> = 1 MHz)	fΤ	_	30	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	C <sub>ob</sub>	_		600	pF

<sup>(1)</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2%.

# **TYPICAL CHARACTERISTICS**

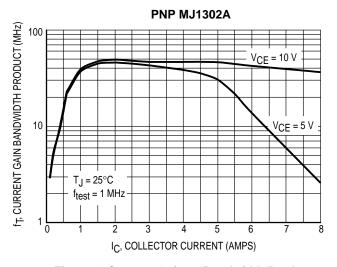


Figure 1. Current-Gain — Bandwidth Product

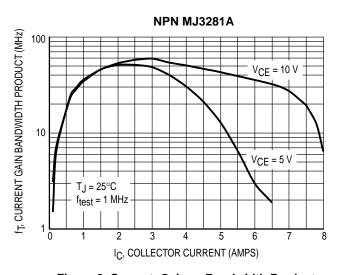


Figure 2. Current-Gain — Bandwidth Product

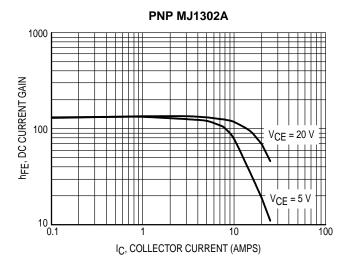


Figure 3. DC Current Gain

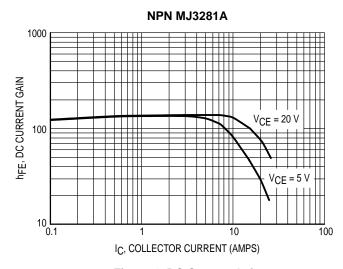


Figure 4. DC Current Gain

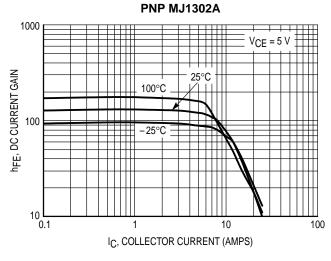


Figure 5. DC Current Gain, VCE = 5 V

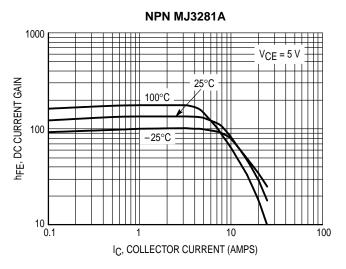


Figure 6. DC Current Gain, VCE = 5 V

### TYPICAL CHARACTERISTICS

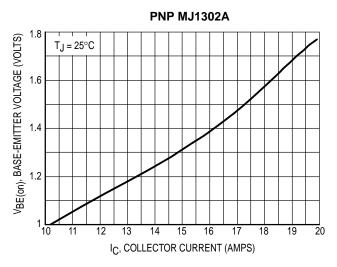
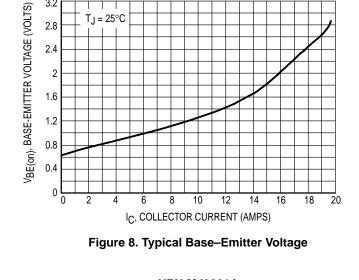


Figure 7. Typical Base-Emitter Voltage



NPN MJ3281A

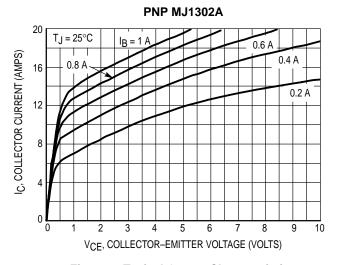
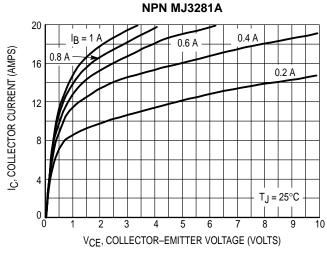


Figure 9. Typical Output Characteristics



**Figure 10. Typical Output Characteristics** 

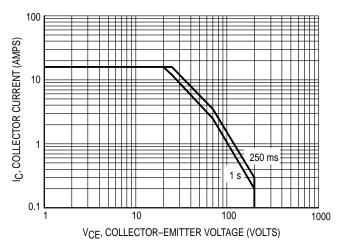
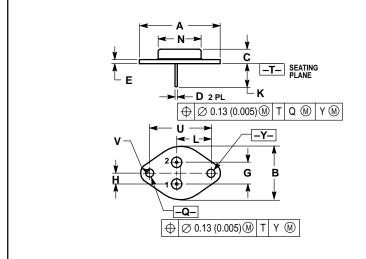


Figure 11. Forward Bias Safe Operating Area (FBSOA)

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate IC - VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on  $T_{J(pk)} = 200^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

# **PACKAGE DIMENSIONS**



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	1.550 REF		39.37 REF			
В	-	1.050		26.67		
С	0.250	0.335	6.35	8.51		
D	0.038	0.043	0.97	1.09		
Е	0.055	0.070	1.40	1.77		
G	0.430	0.430 BSC		10.92 BSC		
Н	0.215	BSC	5.46 BSC			
K	0.440	0.480	11.18	12.19		
L	0.665 BSC		16.89 BSC			
N		0.830		21.08		
Q	0.151	0.165	3.84	4.19		
U	1.187 BSC		30.15 BSC			
v	0 131	0.188	3 33	4 77		

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

**CASE 1-07** TO-204AA (TO-3) ISSUE Z

#### MJ3281A MJ1302A

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How to reach us:

**USA/EUROPE**: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

**HONG KONG:** Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



